ICMOVPE XXII July 12-17, 2026 ICC JEJU, Jeju Island, Korea

Session Title:	**[ThA1] Al-rich AlGaN**
Session Date:	**July 16 (Thu.), 2026**
Session Time:	**08:30-09:45**
Session Room:	**Room A (Baekrok Hall B-1, 1F)**
Session Chairs	

[ThA1-1] **08:30-08:45**

Interface Engineering on Enhancement-Mode Al-Rich $Al_{0.8}Ga_{0.2}N$ MOSFET Enabled by Atomic Layer Etching

Tingang Liu, Haicheng Cao, Mingtao Nong, and Xiaohang Li, King Abdullah University of Science and Technology, Saudi Arabia

[ThA1-2] **08:45-09:00**

Impact of AlN/AlGaN Superlattice Structure on Proton-Induced Transport in Al-Rich AlGaN Channel HEMTs from Room Temperature to 500 ℃

Shyam Mohan, Joocheol Jeong, Jaejin Heo, Hyogeun Cho, Mingoo Jo, Minyeong Kim, and Okhyun Nam, Tech University of Korea, Korea

[ThA1-3] **09:00-09:15**

Formation of Low-Resistance Ohmic Contacts to Al-Rich AlGaN Using Compositionally Graded n-AlGaN

Riku Ando, Ryota Akaike, Shozabro Tanaka, Hiroki Yasunaga, Takao Nakamura, and Hideto Miyake, Mie University, Japan

[ThA1-4] **09:15-09:30**

Investigation of Low-Resistivity Au-Free Metal Contact on n-Type AlxGa1-xN (x ≥ 0.8)

Tingang Liu, Haicheng Cao, Mingtao Nong, and Xiaohang Li, King Abdullah University of Science and Technology, Saudi Arabia

[ThA1-5] **09:30-09:45**

High-Temperature and Radiation Responses of Al-Rich AlGaN Channel HEMTs Employing Various Gate Metals

Mingoo Jo[1], Joocheol Jeong[1], Shyam Mohan[1], Jaejin Heo[1], Hyogeun Cho[1], Minyeong Kim[1], Dongseok Kim[2], Jiun Oh[3], Minji Kim[3], and Okhyun Nam[1], [1] Tech University of Korea , Korea, [2] Korea Atomic Energy Research Institute, Korea, [3] Korea Institute of Energy Technology, Korea